74LVC1G86-Q100
2-input EXCLUSIVE-OR gate

Rev. 4 — 7 January 2022

Product data sheet

1. General description

The 74LVC1G86-Q100 provides the 2-input EXCLUSIVE-OR function.

Inputs can be driven from either 3.3 V or 5 V devices. These features allow the use of these devices in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial Power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from -40 °C to +85 °C and -40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Overvoltage tolerant inputs to 5.5 V
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8C (2.7 V to 3.6 V)
  - JESD36 (4.5 V to 5.5 V)
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power dissipation
- I_{OFF} circuitry provides partial Power-down mode operation
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels

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3. Ordering information

Table 1. Ordering information

| Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G86GW-Q100	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G86GV-Q100	-40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
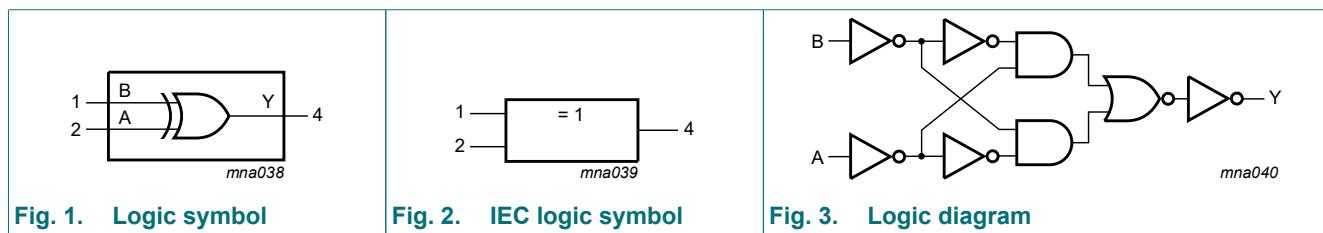
4. Marking

Table 2. Marking codes

Type number	Marking[1]
74LVC1G86GW-Q100	VH
74LVC1G86GV-Q100	V86
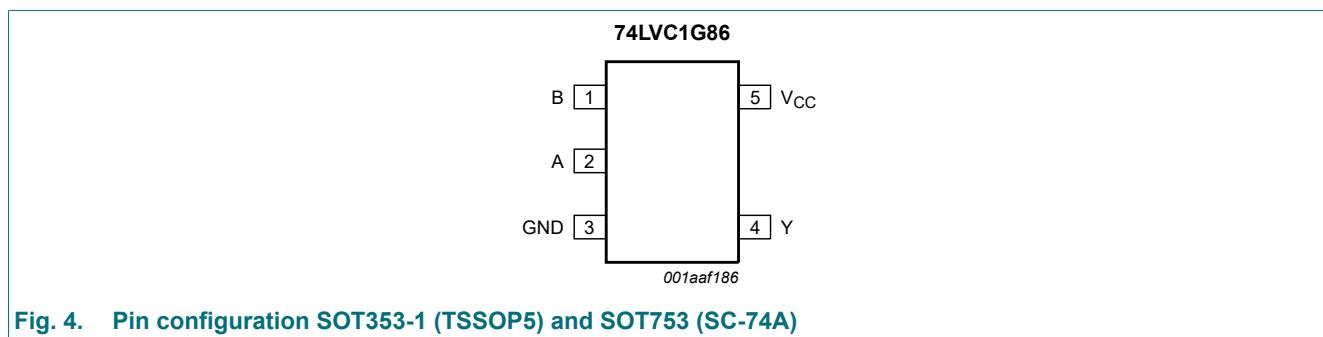
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

Fig. 1. Logic symbol

Fig. 2. IEC logic symbol

Fig. 3. Logic diagram

6. Pinning information

6.1. Pinning

Fig. 4. Pin configuration SOT353-1 (TSSOP5) and SOT753 (SC-74A)

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6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description
B	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V_{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

Input		Output
A	**B**	**Y**
L	L	L
L	H	H
H	L	H
H	H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		-50	-	mA
V_I	input voltage		[1]	-0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		-	±50	mA
V_O	output voltage	Active mode	[1]	-0.5	V_{CC} + 0.5	V
		Power-down mode; $V_{CC} = 0$ V	[1]	-0.5	+6.5	V
I_O	output current	$V_O = 0$ V to V_{CC}		-	±50	mA
I_{CC}	supply current			-	+100	mA
I_{GND}	ground current			-100	-	mA
P_{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C	[2]	-	250	mW
T_{stg}	storage temperature			-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
[2] For SOT353-1 (TSSOP5) package: P_{tot} derates linearly with 3.3 mW/K above 74 °C.
For SOT753 (SC-74A) package: P_{tot} derates linearly with 3.8 mW/K above 85 °C.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	V_{CC}	V
		V_{CC} = 0 V; Power-down mode	0	-	5.5	V
T_{amb}	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65V_{CC}	-	-	0.65V_{CC}	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7V_{CC}	-	-	0.7V_{CC}	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35V_{CC}	-	0.35V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3V_{CC}	-	0.3V_{CC}	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = -100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} - 0.1	-	-	V_{CC} - 0.1	-	V
		I_O = -4 mA; V_{CC} = 1.65 V	1.2	-	-	0.95	-	V
		I_O = -8 mA; V_{CC} = 2.3 V	1.9	-	-	1.7	-	V
		I_O = -12 mA; V_{CC} = 2.7 V	2.2	-	-	1.9	-	V
		I_O = -24 mA; V_{CC} = 3.0 V	2.3	-	-	2.0	-	V
		I_O = -32 mA; V_{CC} = 4.5 V	3.8	-	-	3.4	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.10	-	0.10	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	-	0.45	-	0.70	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	-	0.30	-	0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	-	0.40	-	0.60	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	-	0.55	-	0.80	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	-	0.55	-	0.80	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	±0.1	±1	-	±1	μA
I_{OFF}	power-off leakage current	V_{CC} = 0 V; V_I or V_O = 5.5 V	-	±0.1	±2	-	±2	μA

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Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
I_{CC}	supply current	V_I = 5.5 V or GND; I_O = 0 A; V_{CC} = 1.65 V to 5.5 V	-	0.1	4	-	4	µA
ΔI_{CC}	additional supply current	per pin; V_{CC} = 2.3 V to 5.5 V; $V_I = V_{CC}$ - 0.6 V; I_O = 0 A	-	5	500	-	500	µA
C_I	input capacitance	V_{CC} = 3.3 V; V_I = GND to V_{CC}	-	5	-	-	-	pF

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6.

Symbol	Parameter	Conditions		-40 °C to +85 °C			-40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	A, B to Y; see Fig. 5	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.7	9.9	1.0	13.0	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.5	5.5	0.5	7.0	ns
		V_{CC} = 2.7 V		0.5	2.8	5.8	0.5	7.5	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.3	5.0	0.5	6.5	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.9	4.0	0.5	5.5	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC}	[3]						
		V_{CC} = 3.3 V		-	25	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.
[2] t_{pd} is the same as t_{PLH} and t_{PHL}
[3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
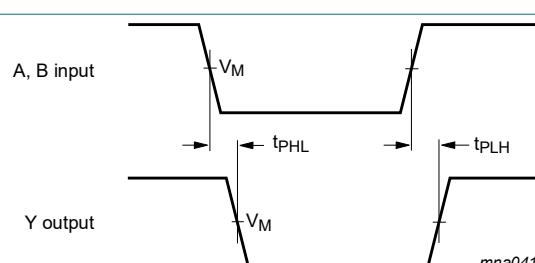
11.1. Waveforms and test circuit
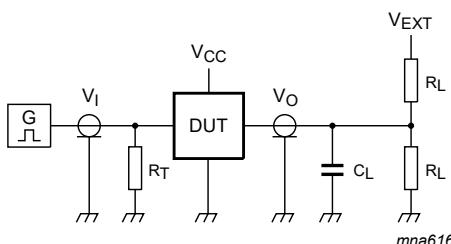
Measurement points are given in Table 9.
V_{OL} and V_{OH} are typical output voltage levels that occur with the output.

Fig. 5. The input A and B to output Y propagation delay times

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Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5V_{CC}$	$0.5V_{CC}$
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$

Test data is given in Table 10.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator;

C_L = Load capacitance including jig and probe capacitance;

R_L = Load resistance;

V_{EXT} = External voltage for measuring switching times.
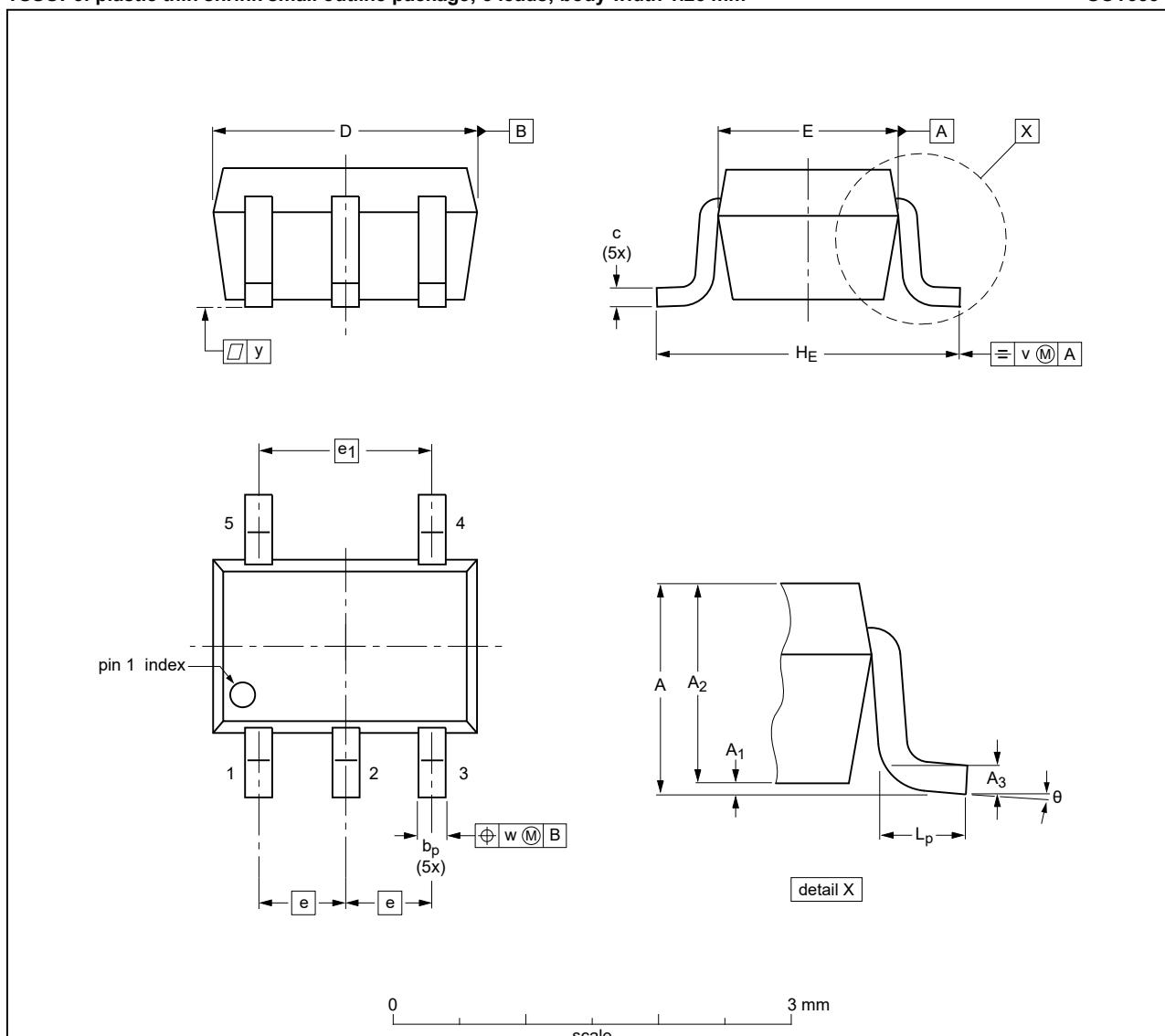
Fig. 6.   Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load			V_{EXT}
V_{CC}	V_I	$t_r = t_f$	C_L	R_L		t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ		open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω		open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω		open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω		open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω		open

12. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm   **SOT353-1**

Dimensions (mm are the original dimensions)

Unit		A	A₁	A₂	A₃	bₚ	c	D(1)	E(1)	e	e₁	H_E	L_p	v	w	y	θ
mm	max	1.1	0.1	1.0	0.15	0.30	0.25	2.2	1.35	0.65	1.3	2.4	0.46	0.3	0.1	0.1	8°
	min	0.8	0	0.8		0.15	0.08	1.8	1.15			1.8	0.26				0°

Note
1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

sot353-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT353-1		MO-203	SC-88A			~~21-12-15~~ 21-12-16

Fig. 7.   Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

DIMENSIONS (mm are the original dimensions)

UNIT	A	A$_1$	b$_p$	c	D	E	e	H$_E$	L$_p$	Q	v	w	y
mm	1.1 0.9	0.100 0.013	0.40 0.25	0.26 0.10	3.1 2.7	1.7 1.3	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT753			SC-74A			02-04-16 06-03-16
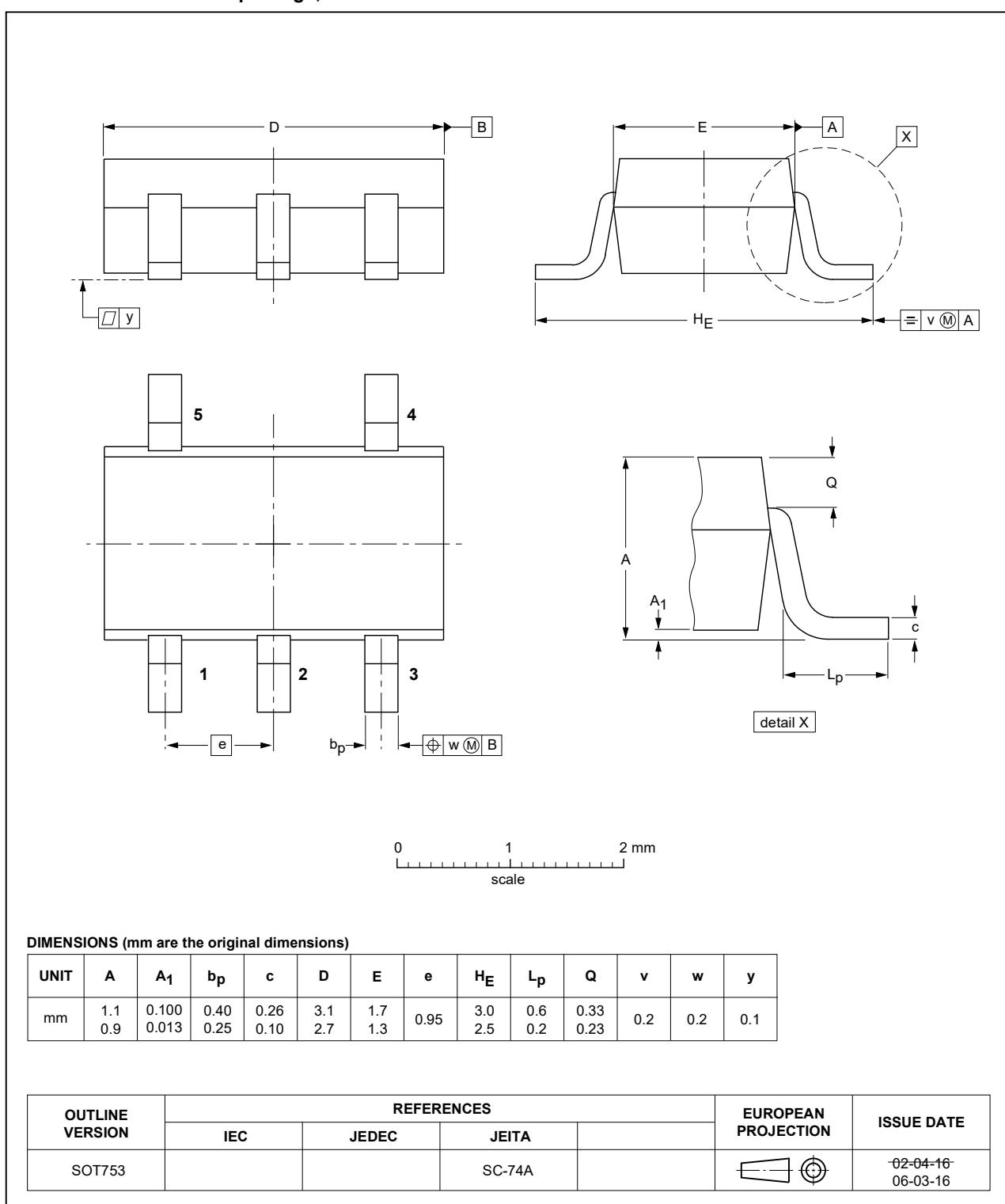
Fig. 8.   Package outline SOT753 (SC-74A)

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G86_Q100 v.4	20220107	Product data sheet	-	74LVC1G86_Q100 v.3
Modifications:	• Table 5: Derating values for P_{tot} total power dissipation updated. • Fig. 7: Package outline drawing for SOT353-1 (TSSOP5) has changed. • Section 2 updated.			
74LVC1G86_Q100 v.3	20170307	Product data sheet	-	74LVC1G86_Q100 v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. • Legal texts have been adapted to the new company name where appropriate.			
74LVC1G86_Q100 v.2	20161212	Product data sheet	-	74LVC1G86_Q100 v.1
Modifications:	• Table 7: The maximum limits for leakage current and supply current have changed.			
74LVC1G86_Q100 v.1	20131115	Product data sheet	-	-

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